

8A Avg.

100 Volts

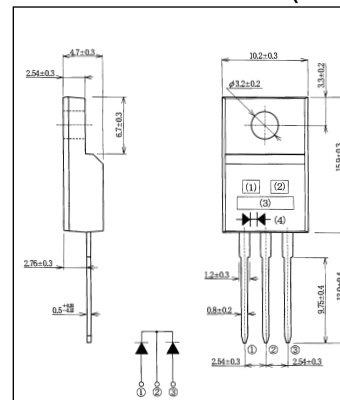
SBD

FCH08U10

■最大定格 Maximum Ratings

Item	Symbol	Conditions			Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	100			V
平均整流電流 Average Rectified Forward Current	I_O	50Hz、正弦全波通電抵抗負荷 50Hz Full Sine Wave Resistive Load	$T_c=127^{\circ}C$	8	A
実効順電流 R.M.S. Forward Current	$I_F(RMS)$	8.89			A
サージ順電流 Surge Forward Current	I_{FSM}	100	50Hz正弦全波、1サイクル、非くり返し 50Hz Full Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	-40~+150			°C
保存温度範囲 Storage Temperature Range	T_{stg}	-40~+150			°C
締付トルク Mounting torque	F_{tor}	推奨値 Recommended Value			0.5 N・m

■ **OUTLINE DRAWING(mm)**



■ APPROX. NET WEIGHT: 2.20g

■電氣的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j = 25^{\circ}\text{C}$, $V_{RM} = V_{RRM}$, 一素子あたり Per Diode	—	—	1	mA
ピーク順電圧 Peak Forward Voltage	V_{FM}	$T_j = 25^{\circ}\text{C}$, $I_{FM} = 4\text{A}$, 一素子あたり Per Diode	—	—	0.88	V
熱抵抗 Thermal Resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to Case	—	—	3.0	$^{\circ}\text{C/W}$
	$R_{th(c-f)}$	ケース・フィン間 Case to Fin	—	—	1.5	$^{\circ}\text{C/W}$

■定格・特性曲線

FIG.1

順電壓特性
FORWARD CURRENT VS. VOLTAGE

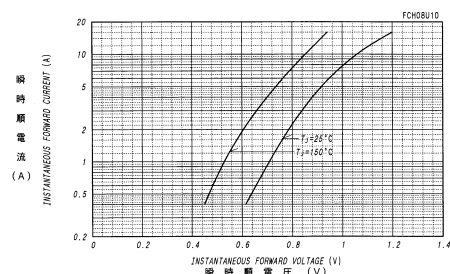


FIG.2

平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION

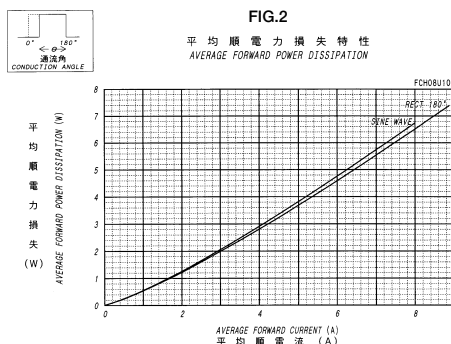


FIG.3

ピーク逆電流 — ピーク逆電圧特性
PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE
Tj = 150°C

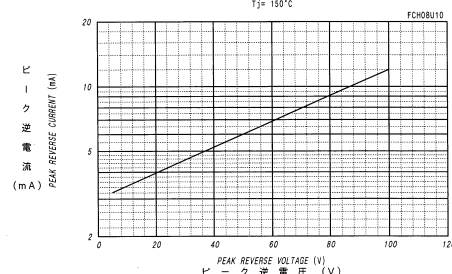


FIG.4

平均逆電力損失
AVERAGE REVERSE POWER DISSIPATION

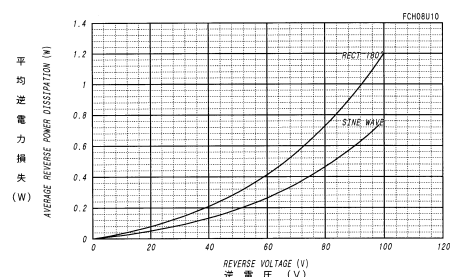


FIG.5

平均順電流—ケース温度定格
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE
V_{RM}=100V

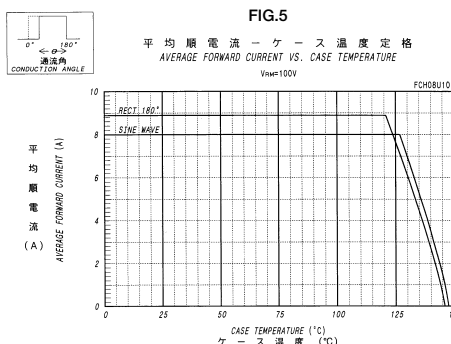


FIG.6

サージ順電流定格
SURGE CURRENT RATINGS
f=50Hz Sine Wave, Non-Repetitive, No Load

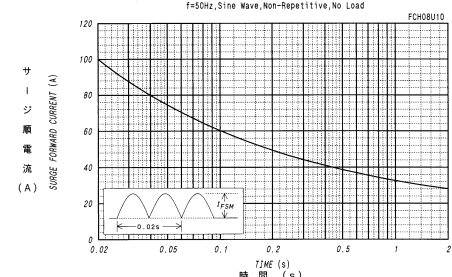


FIG.7

接合容量特性
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE
Tj=25°C, Vm=20nVrms, f=100kHz, Typical Value

